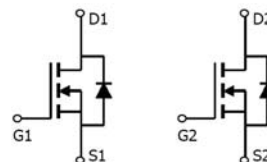


N-Channel Power MOSFET

Description

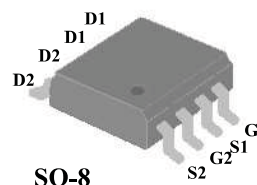
The RMD8N60S8 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.



Schematic diagram

General Features

- $V_{DS} = 60V, I_D = 8A$
 $R_{DS(ON)} < 20m\Omega @ V_{GS}=10V$ (Typ:15m Ω)
 $R_{DS(ON)} < 25m\Omega @ V_{GS}=4.5V$ (Typ:19.5m Ω)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Low gate to drain charge to reduce switching losses



SO-8

pin assignment

Application

- Power switching application
- Load switch
- Halogen-free

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
4846	RMD8N60S8	SOP-8			

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	8	A
Drain Current-Continuous($T_C=100^{\circ}C$)	$I_D(100^{\circ}C)$	6.5	A
Pulsed Drain Current	I_{DM}	32	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	85	$^{\circ}C/W$
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Electrical Characteristics (TC=25°C unless otherwise noted)

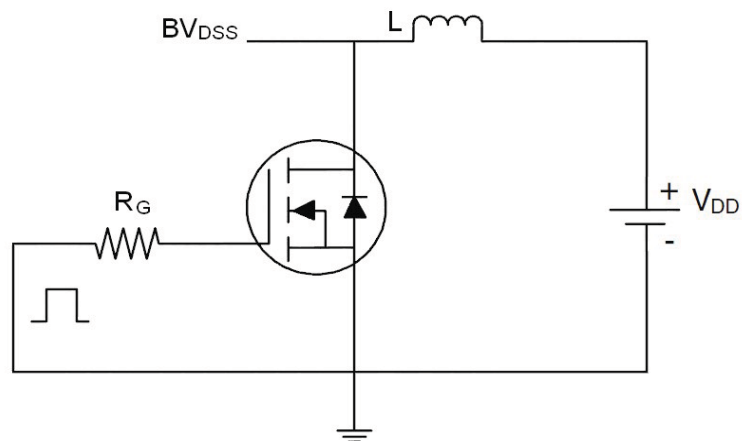
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.2	1.8	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7A	-	15	20	mΩ
		V _{GS} =4.5V, I _D =5A	-	19.5	25	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =9A	25	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{Iss}	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	2180	-	PF
Output Capacitance	C _{Oss}		-	350	-	PF
Reverse Transfer Capacitance	C _{rss}		-	270	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, R _L =1Ω V _{GS} =10V,R _{GEN} =3Ω	-	8.5	-	nS
Turn-on Rise Time	t _r		-	6	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Q _g	V _{DS} =30V,I _D =8A, V _{GS} =10V	-	58	-	nC
Gate-Source Charge	Q _{gs}		-	8	-	nC
Gate-Drain Charge	Q _{gd}		-	17	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =9A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S	-	-	-	7	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF=9A	-	30	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs ^(Note3)	-	44	-	nC

Notes:

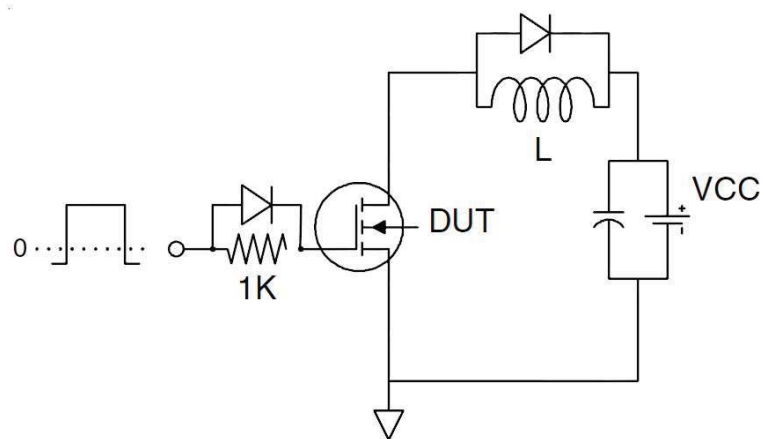
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

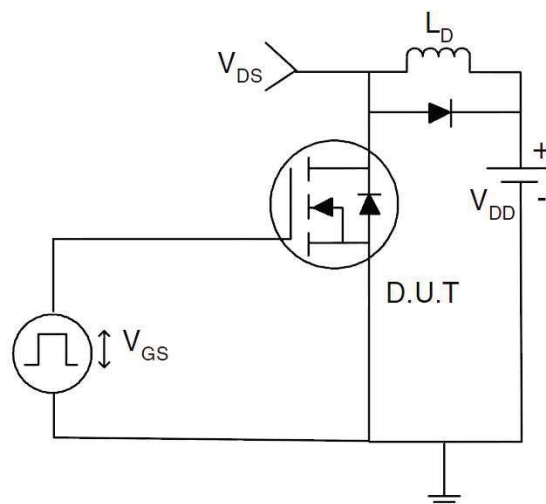
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



RATING AND CHARACTERISTICS CURVES (RMD8N60S8)

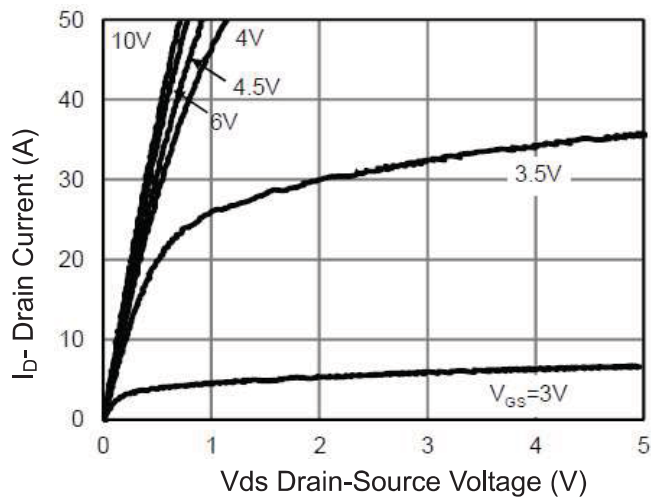


Figure 1 Output Characteristics

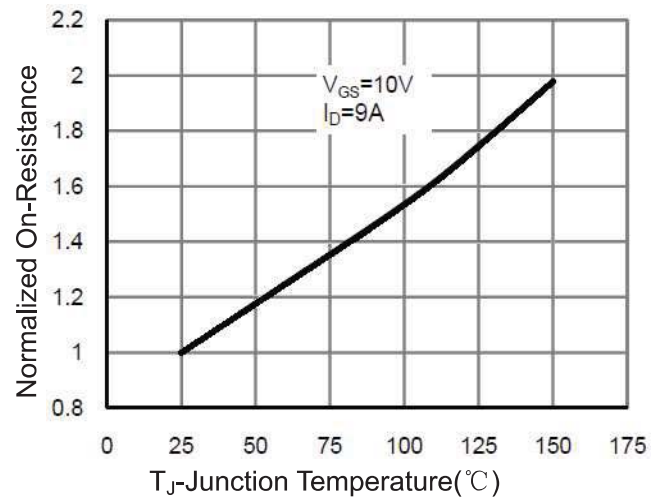


Figure 4 Rdson-Junction Temperature

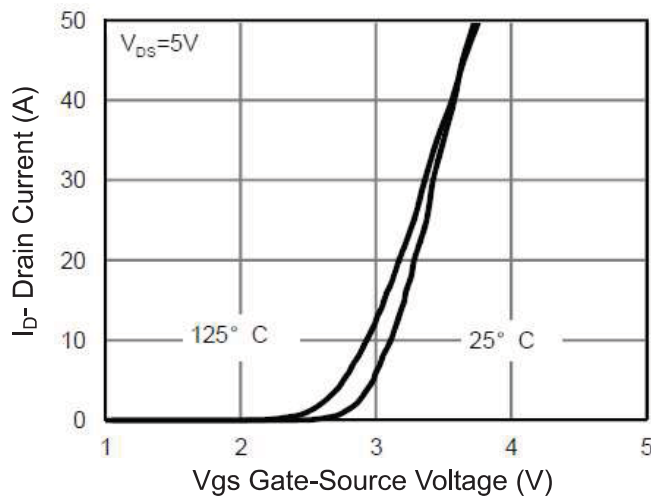


Figure 2 Transfer Characteristics

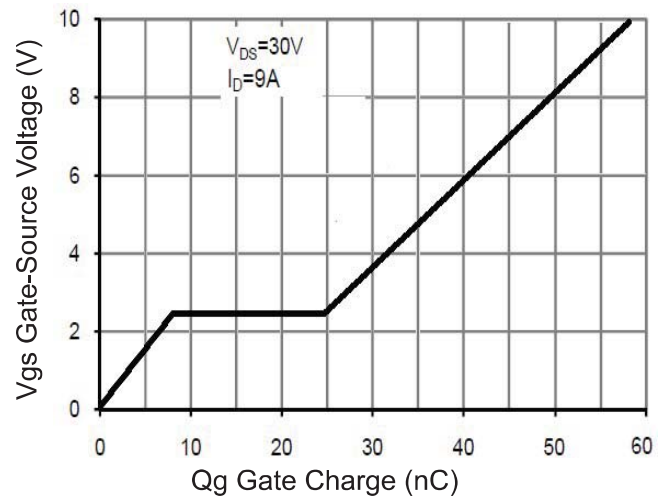


Figure 5 Gate Charge

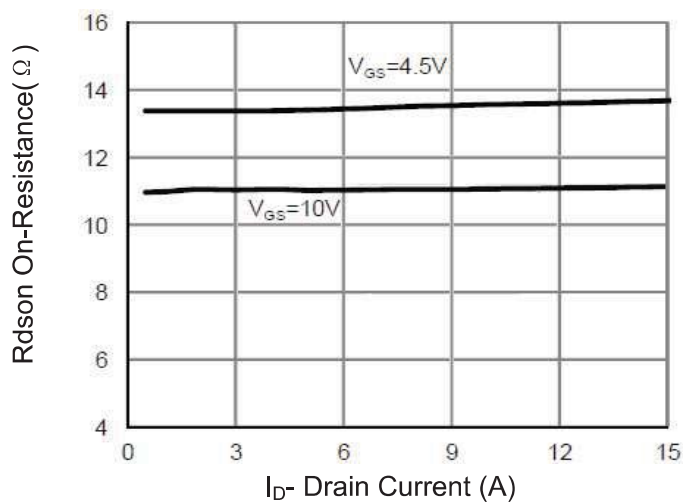


Figure 3 Rdson- Drain Current

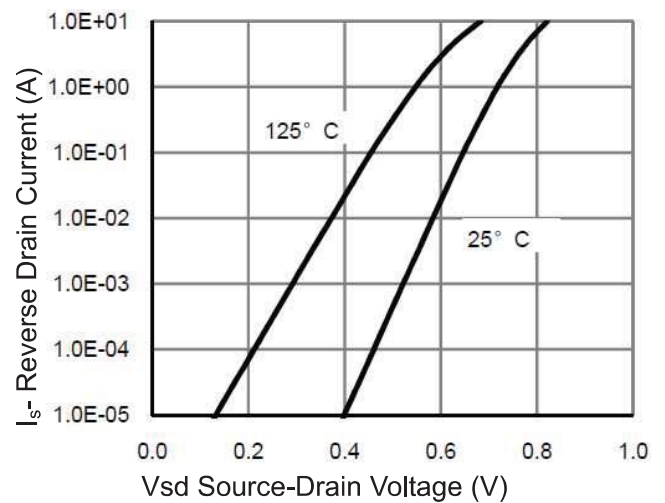


Figure 6 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RMD8N60S8)

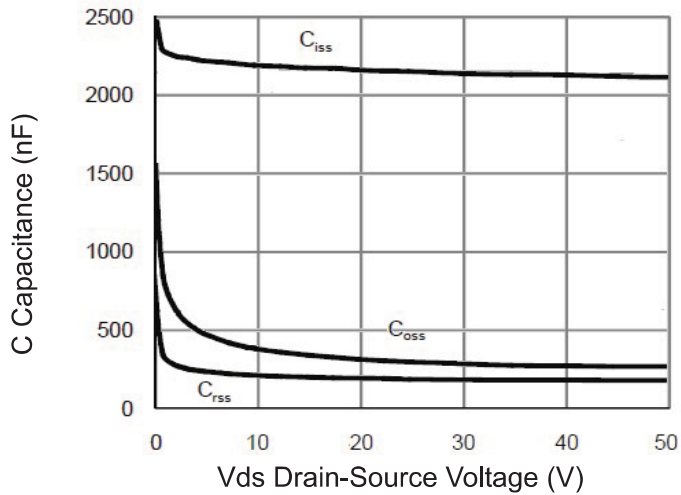


Figure 7 Capacitance vs Vds

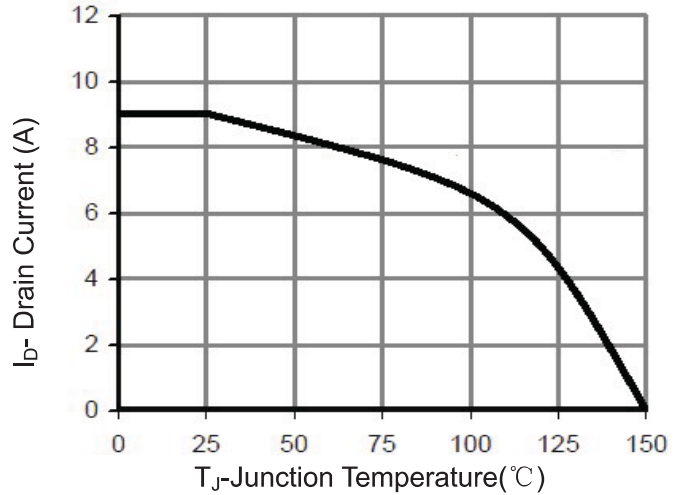


Figure 9 Current De-rating

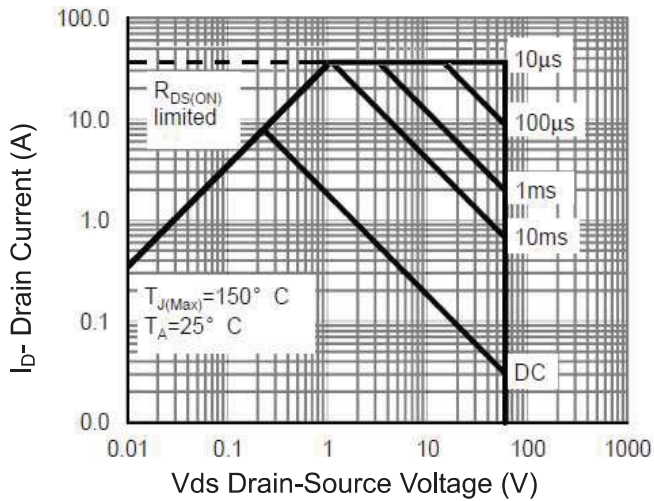


Figure 8 Safe Operation Area

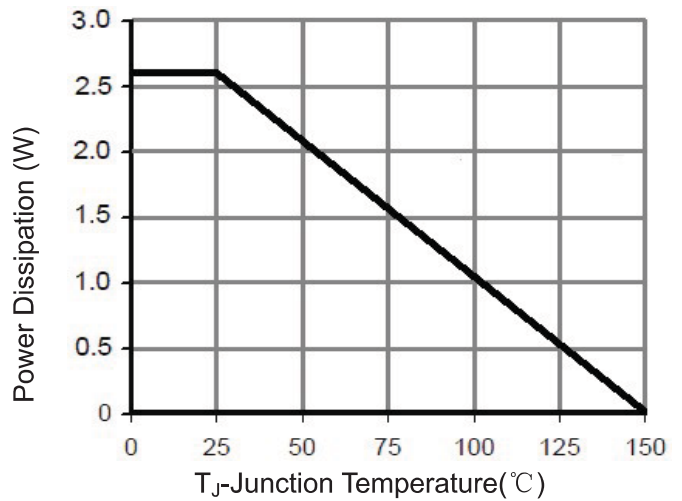


Figure 10 Power De-rating

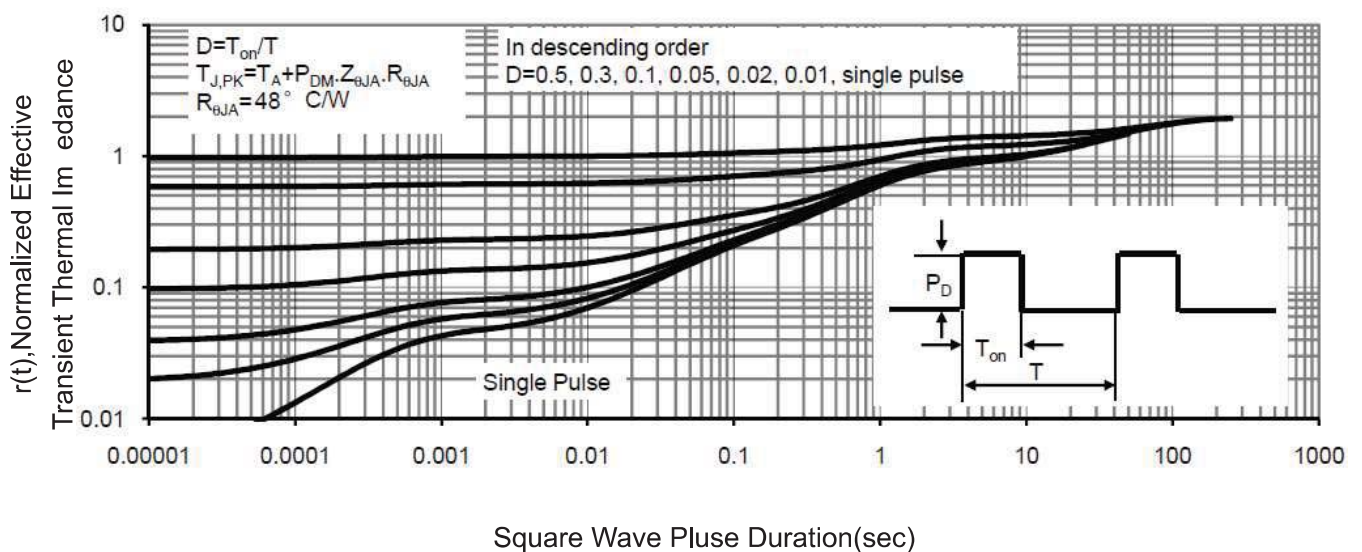
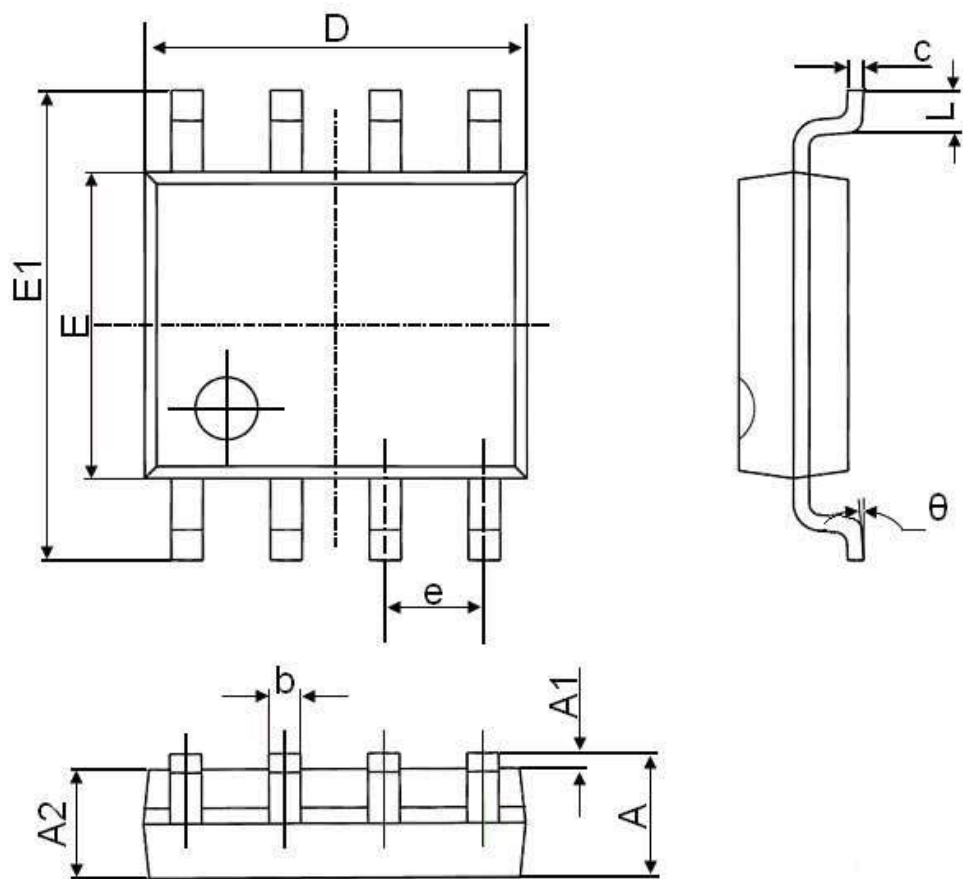


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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